



## Si3863BDV vs. Si3863DV

**Description:** Load Switch with Level-Shift  
**Package:** TSOP-6  
**Pin Out:** Identical

**Part Number Replacements:**

Si3863BDV-T1-E3 Replaces Si3863DV-T1-E3  
 Si3863BDV-T1-E3 Replaces Si3863DV-T1

**Summary of Performance:**

The Si3863BDV is an upgrade to the original Si3863DV; both parts perform identically, including limits to the parametric tables below.

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED)				
Parameter	Symbol	Si3863BDV	Si3863DV	Unit
Input Voltage	V <sub>IN</sub>	12	12	V
ON/OFF Voltage	V <sub>ON/OFF</sub>	8	8	
Load Current	Continuous	±2.5	±2.5	A
	Pulsed	±5	±5	
Continuous Intrinsic Diode Conduction	I <sub>S</sub>	-1	-1	
Power Dissipation	P <sub>D</sub>	0.83	0.83	W
Operating Junction & Storage Temperature Range	T <sub>j</sub> & T <sub>stg</sub>	-55 to 150	-55 to 150	°C
Maximum Junction-to-Ambient	R <sub>thJA</sub>	150	150	°C/W

SPECIFICATIONS (T <sub>J</sub> = 25°C UNLESS OTHERWISE NOTED)									
Parameter	Symbol	Si3863BDV			Si3863DV			Unit	
		Min	Typ	Max	Min	Typ	Max		
<b>OFF Characteristic</b>									
Reverse Leakage Current	I <sub>FL</sub>			1			1		µA
Diode Forward Voltage	V <sub>SD</sub>		-0.75	-1		-0.75	-1		V
<b>Dynamic</b>									
Input Voltage Range	V <sub>IN</sub>	2.5		12	2.5		12		nC
On-Resistance (p-channel) @ 1A	V <sub>IN</sub> = 4.5 V		0.057	0.075		0.086	0.105		Ω
	V <sub>IN</sub> = 3.0 V		0.082	0.105		0.105	0.125		Ω
	V <sub>IN</sub> = 2.5 V		0.110	0.140		0.135	0.165		Ω
On-State (p-channel) Drain-Current	V <sub>IN</sub> = 10 V	1			1				A
	V <sub>IN</sub> = 5 V	1			1				A